

Diode

Silicon Carbide Schottky Diode

IDM10G120C5

5th Generation thinQ!™ 1200 V SiC Schottky Diode

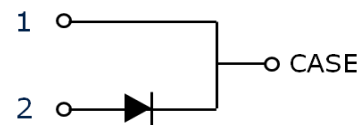
Final Datasheet

Rev. 2.0 2015-22-07

SiC Schottky Diode

Features:

- Revolutionary semiconductor material - Silicon Carbide
- No reverse recovery current / No forward recovery
- Temperature independent switching behavior
- Low forward voltage even at high operating temperature
- Tight forward voltage distribution
- Excellent thermal performance
- Extended surge current capability
- Specified dv/dt ruggedness
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant



Benefits

- System efficiency improvement over Si diodes
- System cost / size savings due to reduced cooling requirements
- Enabling higher frequency / increased power density solutions
- Higher system reliability due to lower operating temperatures
- Reduced EMI
- Related Links: www.infineon.com/sic



Applications

- Solar inverters
- Uninterruptable power supplies
- Motor drives
- Power Factor Correction



Package pin definitions

- Pin 1 and backside – cathode
- Pin 2 – anode

Key Performance and Package Parameters

Type	V_{DC}	I_F	Q_C	$T_{j,max}$	Marking	Package
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1) J-STD20 and JESD22

IDM10G120C5	1200V	10A	41nC	175°C	D1012C5	PG-TO252-2
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Maximum ratings

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	1200	V
Continuous forward current for $R_{th(j-c,max)}$ $T_C = 160^\circ\text{C}$, D=1 $T_C = 135^\circ\text{C}$, D=1 $T_C = 25^\circ\text{C}$, D=1	I_F	10 18 38	A
Surge non-repetitive forward current, sine halfwave $T_C=25^\circ\text{C}$, $t_p=10\text{ms}$ $T_C=150^\circ\text{C}$, $t_p=10\text{ms}$	$I_{F,SM}$	99 84	
Non-repetitive peak forward current $T_C = 25^\circ\text{C}$, $t_p=10 \mu\text{s}$	$I_{F,max}$	711	
i^2t value $T_C = 25^\circ\text{C}$, $t_p=10 \text{ ms}$ $T_C = 150^\circ\text{C}$, $t_p=10 \text{ ms}$	$\int i^2 dt$	49 35	A^2s
Diode dv/dt ruggedness $V_R=0\ldots 960 \text{ V}$	dv/dt	80	V/ns
Power dissipation $T_C = 25^\circ\text{C}$	P_{tot}	223	W
Operating temperature	T_j	-55...175	$^\circ\text{C}$
Storage temperature	T_{stg}	-55...150	
Soldering temperature, Wave- and reflowsoldering allowed (reflow MSL1)	T_{sold}	260	

Thermal Resistances

Thermal Resistances						
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Characteristic						
Diode thermal resistance, junction – case	$R_{th(j-c)}$		-	0.5	0.7	K/W
Thermal resistance, junction – ambient	$R_{th(j-a)}$	SMD version, device on PCB, minimal footprint	-	-	62	
		SMD version, device on PCB, 6 cm ² cooling area ²⁾		35		

²⁾ Device on 40 mm*40mm*1.5 epoxy PCB FR4 with 6cm² (one layer, 70µm thick) copper for cathode connection. PCB is vertical without air stream cooling.

Electrical Characteristics

Static Characteristic, at T_j=25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
DC blocking voltage	V _{DC}	T _j = 25°C	1200	-	-	V
Diode forward voltage	V _F	I _F = 10 A, T _j = 25°C	-	1.5	1.8	V
		I _F = 10 A, T _j = 150°C	-	2.0	2.6	
Reverse current	I _R	V _R = 1200 V, T _j = 25°C		4	62	μA
		V _R = 1200 V, T _j = 150°C		22	320	

Dynamic Characteristics, at T_j=25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Total capacitive charge	Q _C	V _R = 800 V, T _j = 150°C $Q_C = \int_0^{V_R} C(V) dV$	-	41	-	nC
Total Capacitance	C	V _R = 1 V, f = 1 MHz	-	525	-	pF
		V _R = 400 V, f = 1 MHz	-	37	-	
		V _R = 800 V, f = 1 MHz	-	29	-	

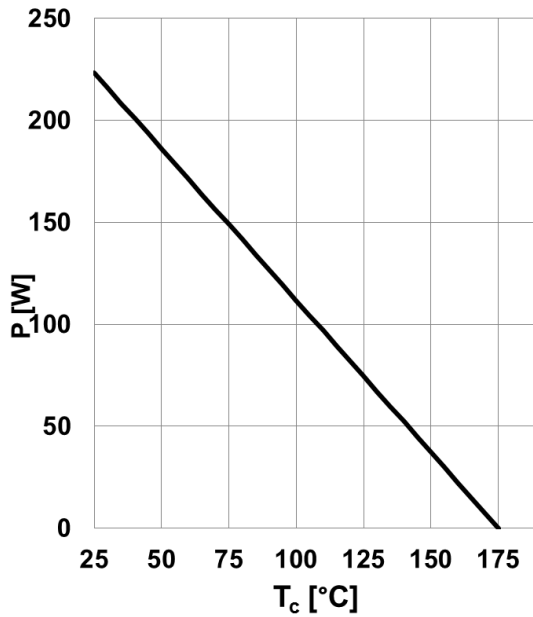


Figure 1. **Power dissipation as a function of case temperature, $P_{tot}=f(T_c)$, $R_{th(j-c),max}$**

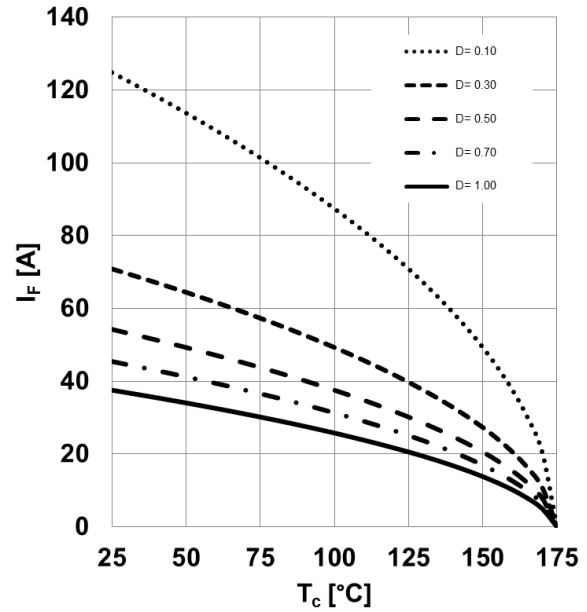


Figure 2. **Diode forward current as function of temperature, $T_j \leq 175^\circ\text{C}$, $R_{th(j-c),max}$, parameter D =duty cycle, V_{th} , R_{diff} @ $T_j=175^\circ\text{C}$**

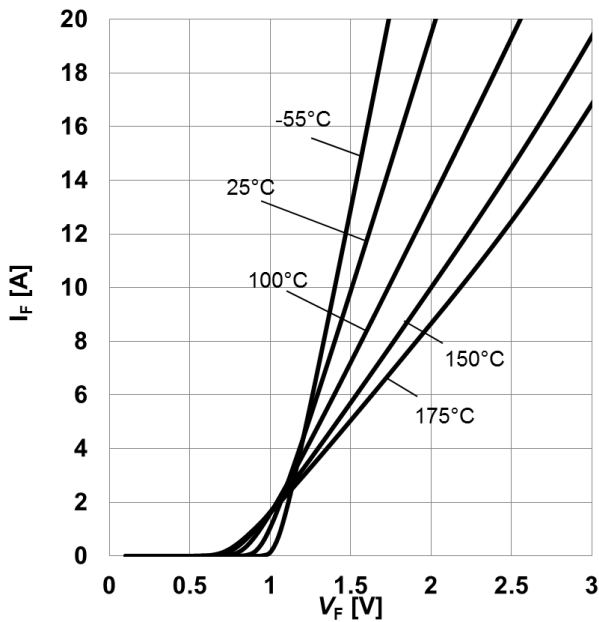


Figure 3. **Typical forward characteristics, $I_F=f(V_F)$, $t_p=10\text{ }\mu\text{s}$, parameter: T_j**

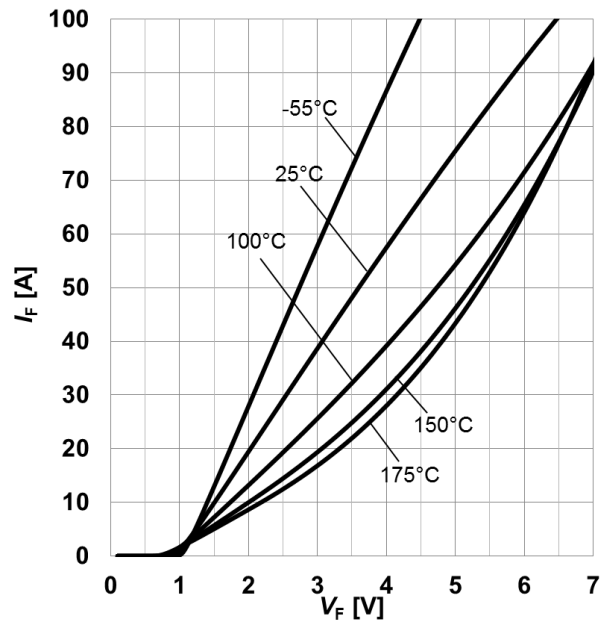


Figure 4. **Typical forward characteristics in surge current, $I_F=f(V_F)$, $t_p=10\text{ }\mu\text{s}$, parameter: T_j**

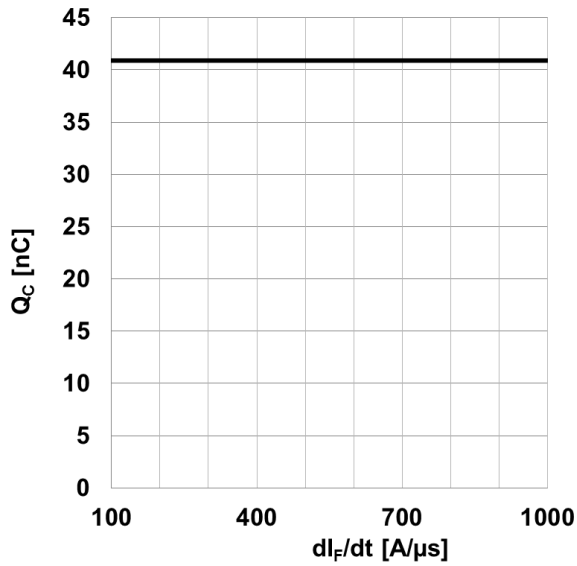


Figure 5. Typical capacitance charge as function of current slope¹, $Q_C=f(di_F/dt)$, $T_J=150^\circ\text{C}$
1) Only capacitive charge, guaranteed by design.

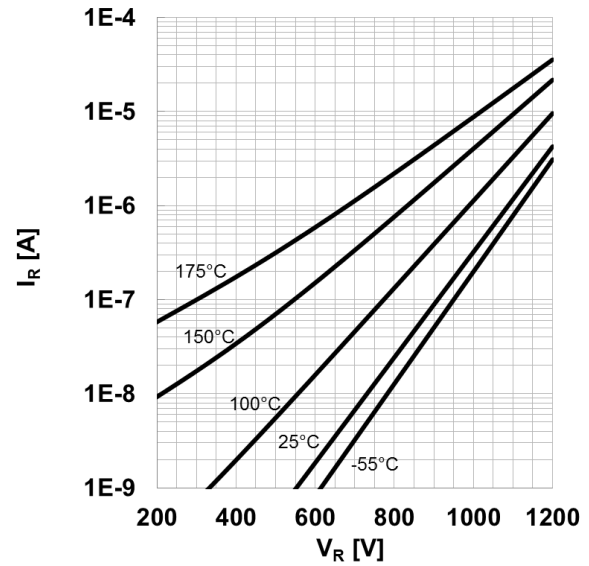


Figure 6. Typical reverse current as function of reverse voltage, $I_R=f(V_R)$, parameter: T_J

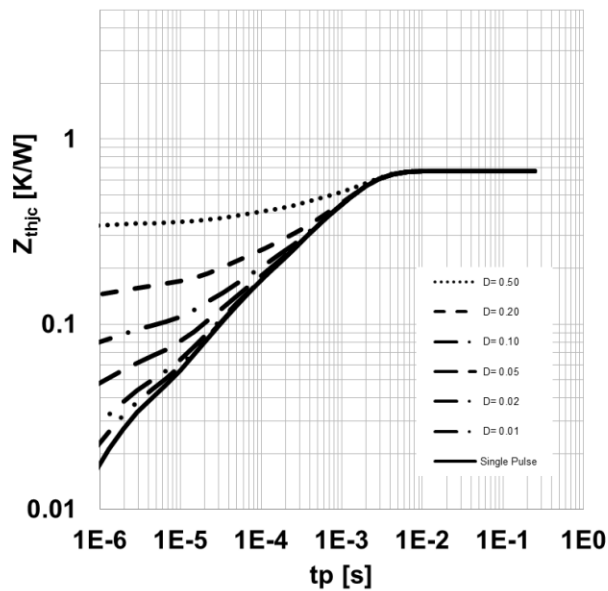


Figure 7. Max. transient thermal impedance, $Z_{th,jc}=f(t_p)$, parameter: $D=t_p/T$

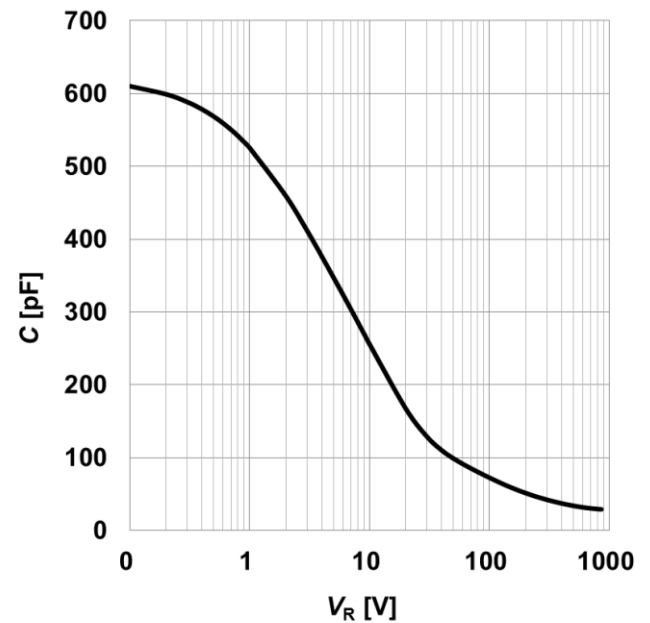


Figure 8. Typical capacitance as function of reverse voltage, $C=f(V_R)$; $T_J=25^\circ\text{C}$; $f=1\text{ MHz}$

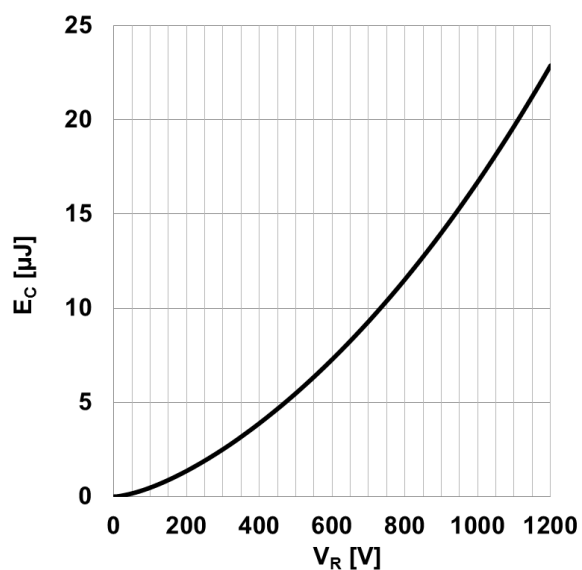
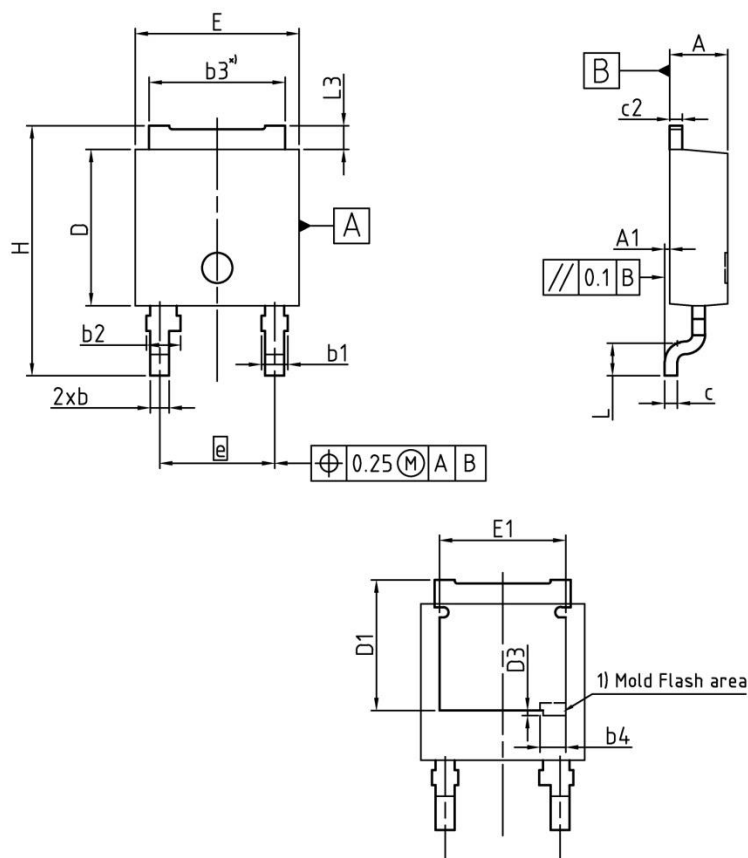


Figure 9. Typical capacitance stored energy as function of reverse voltage,

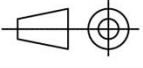
$$E_C = \int_0^{V_R} C(V) V dV$$

PG-TO252-2



*) mold flash not included

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.35	0.087	0.093
A1	0.00	0.15	0.000	0.006
b	0.65	0.85	0.026	0.033
b1	-	1.15	-	0.045
b2	1.05	1.45	0.041	0.057
b3	5.30	5.50	0.209	0.217
b4	1.02		0.040	
c	0.46	0.58	0.018	0.023
c2	0.46	0.58	0.018	0.023
D	6.02	6.22	0.237	0.245
D1	5.04	5.44	0.198	0.214
E	6.45	6.65	0.254	0.262
E1	5.00		0.197	
e	4.57 (BSC)		0.180 (BSC)	
N	2		2	
H	9.40	10.40	0.370	0.409
L	1.19	1.39	0.047	0.055
D3	0.20		0.008	
L3	0.90	1.10	0.035	0.043

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Previous Revision:

Revision	Date	Subjects (major changes since last version)
2.0	-	Final data sheet

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